Quad 2-Input Data Selectors / Multiplexers

High-Performance Silicon-Gate CMOS

The 74HCT157 is identical in pinout to the LS157. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device routes 2 nibbles (A or B) to a single port (Y) as determined by the Select input. The data is presented at the outputs in noninverted form. A high level on the Output Enable input sets all four Y outputs to a low level.

Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 82 FETs or 20.5 Equivalent Gates
- These are Pb-Free Devices



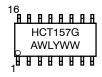
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



74HCT157 = Device Code A = Assembly Location

L, WL = Wafer Lot Y = Year

W, WW = Work Week

G or ■ = Pb-Free Package (Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

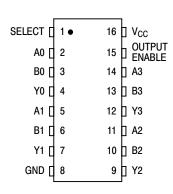


Figure 1. Pin Assignment

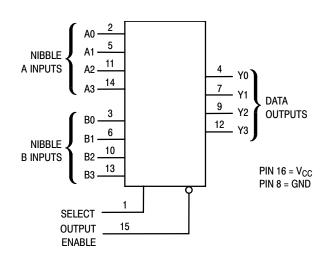


Figure 2. Logic Diagram

FUNCTION TABLE

Inp		
Output Enable	Select	Outputs Y0 – Y3
Н	Х	L
L	L	A0-A3
L	Н	B0-B3

X = don't care A0 – A3, B0 – B3 = the levels of the respective Data–Word Inputs.

ORDERING INFORMATION

Device	Package	Shipping [†]
74HCT157DR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
74HCT157DTR2G	TSSOP-16*	2500 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	$-$ 0.5 to V_{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: $-7 \text{ mW/}^{\circ}\text{C}$ from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)			5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V	
T _A	Operating Temperature, All Package Ty	– 55	+ 125	°C	
t _r , t _f	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	Guaranteed Limit			
Symbol	Parameter	Condition	(V)	-55 to 25°C	≤85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1V$ $ I_{out} \le 20\mu A$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low-Level Input Voltage	$\begin{aligned} V_{out} &= V_{CC} - 0.1V \\ I_{out} &\leq 20 \mu A \end{aligned}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20\mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IL}$ $ I_{out} \le 4.0 \text{mA}$	4.5	3.98	3.84	3.70	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20\mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH}$ $ I_{out} \le 4.0 \text{mA}$	4.5	0.26	0.33	0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$	5.5	4.0	40	40	μΑ
ΔI_{CC}	Additional Quiescent Supply Current	V _{in} = 2.4V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ -55°C	25 to	125°C	
	Guireiii	$V_{in} = V_{CC}$ or GND, Other inputs $I_{out} = 0\mu A$	5.5	2.9	2	.4	mA

^{1.} Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

^{2.} Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

			Guaranteed Limit			
Symbol	Parameter	V _{CC} (V)	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 4)	4.5	21	26	32	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Select to Output Y (Figures 2 and 4)	4.5	22	28	33	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 4)	4.5	20	25	30	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	4.5	15	19	22	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Package)*	33	pF

^{*} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} \, V_{CC}^2 f + I_{CC} \, V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS

A0, A1, A2, A3 (Pins 2, 5, 11, 14)

Nibble A inputs. The data present on these pins is transferred to the outputs when the Select input is at a low level and the Output Enable input is at a low level. The data is presented to the outputs in noninverted form.

B0, B1, B2, B3 (Pins 3, 6, 10, 13)

Nibble B inputs. The data present on these pins is transferred to the outputs when the Select input is at a high level and the Output Enable input is at a low level. The data is presented to the outputs in noninverted form.

OUTPUTS

Y0, Y1, Y2, Y3 (Pins 4, 7, 9, 12)

Data outputs. The selected input Nibble is presented at these outputs when the Output Enable input is at a low level.

The data present on these pins is in its noninverted form. For the Output Enable input at a high level, the outputs are at a low level.

CONTROL INPUTS Select (Pin 1)

Nibble select. This input determines the data word to be transferred to the outputs. A low level on this input selects the A inputs and a high level selects the B inputs.

Output Enable (Pin 15)

Output Enable input. A low level on this input allows the selected input data to be presented at the outputs. A high level on this input sets all outputs to a low level.

SWITCHING WAVEFORMS

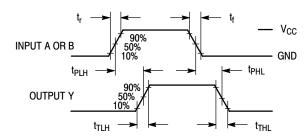


Figure 3. HCT157

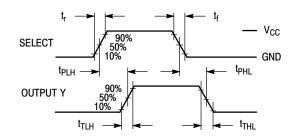


Figure 4. Y versus Selected, Noninverted

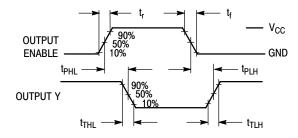
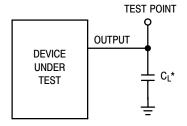


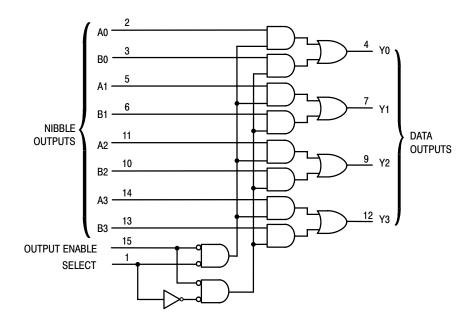
Figure 5. HCT157



*Includes all probe and jig capacitance

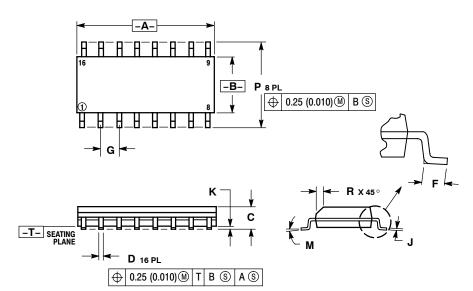
Figure 6. Test Circuit

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS

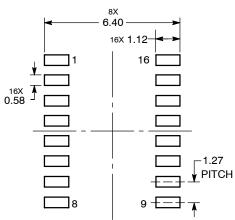
SOIC-16 CASE 751B-05 ISSUE K



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

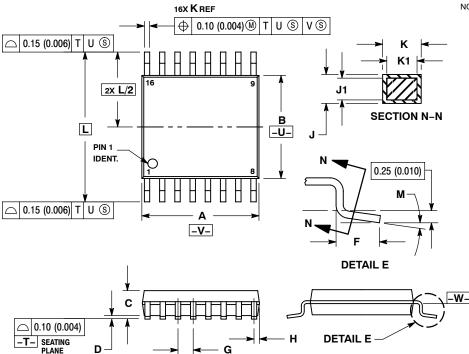


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

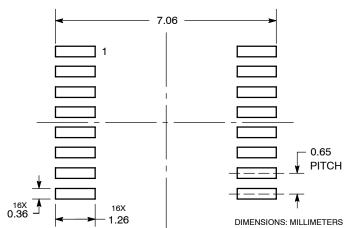
TSSOP-16 CASE 948F-01 ISSUE B



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
 - EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 - NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
М	0°	8 °	0°	8 °

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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